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Team Nexperia

30 V, single N-channel Trench MOSFET 3 August 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low R_{DSon}
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Qu	iick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	30	V
V _{GS}	gate-source voltage	-		-12	-	12	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	1.2	А
Static charac	teristics	1					
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 1.1 A; T _j = 25 °C		-	185	250	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





30 V, single N-channel Trench MOSFET

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G 4 S 017aaa253

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PMV185XN	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

4. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMV185XN	EH%

[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	30	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	1.2	А
		V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	1.1	А
		V_{GS} = 4.5 V; T_{amb} = 100 °C	[1]	-	0.7	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	4.4	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	325	mW
			[1]	-	455	mW
		T _{sp} = 25 °C		-	1275	mW

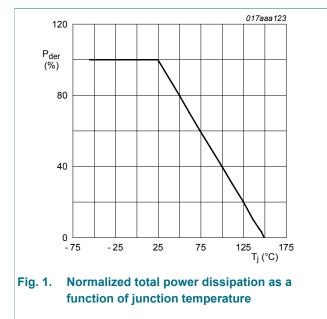
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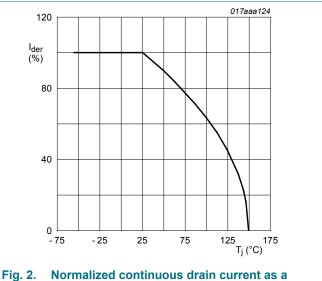
Symbol	Parameter	Conditions		Min	Мах	Unit
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
l _S	source current	T _{amb} = 25 °C	[1]	-	0.7	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



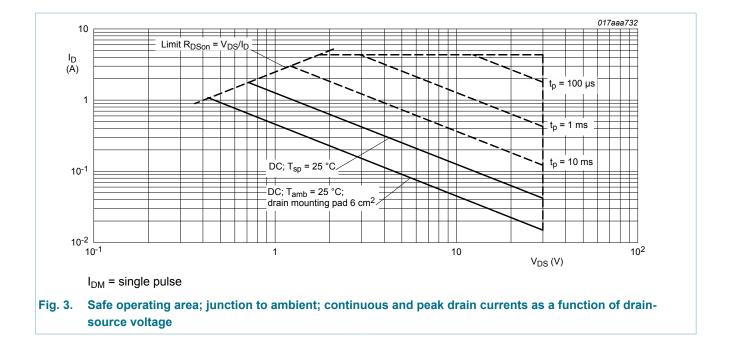
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$





$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \%$$

30 V, single N-channel Trench MOSFET



6. Thermal characteristics

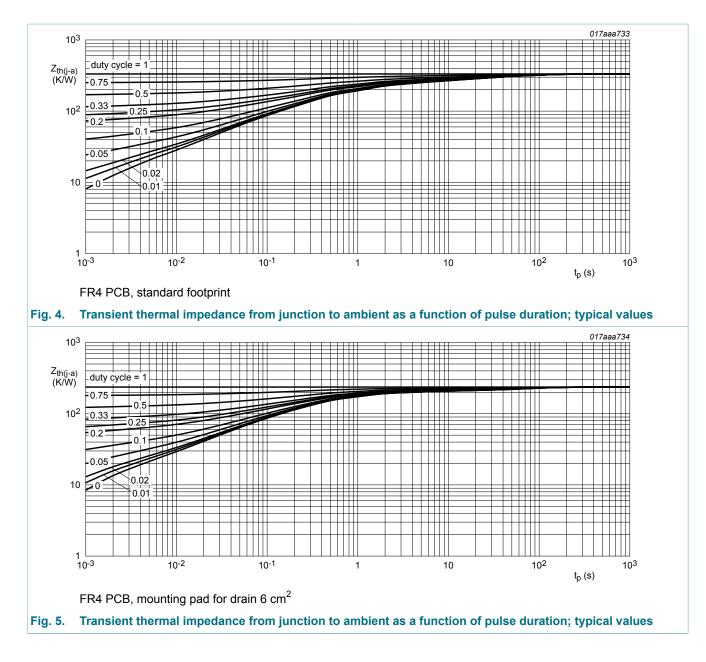
Table 6. 1	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	333	385	K/W
	-		[2]	-	240	275	K/W
	amplent	in free air; t ≤ 5 s	[2]	-	203	235	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	85	100	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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7. Characteristics

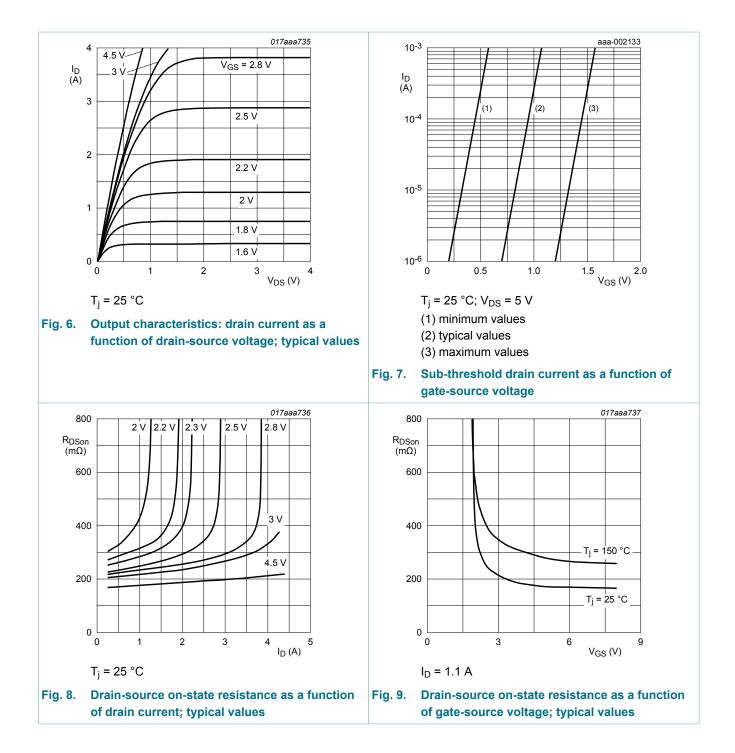
Table 7. Ch	naracteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		30	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C		0.5	1	1.5	V
I _{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_{amb} = 25 °C		-	-	1	μA
		V_{DS} = 30 V; V_{GS} = 0 V; T_{amb} = 150 °C		-	-	10	μA
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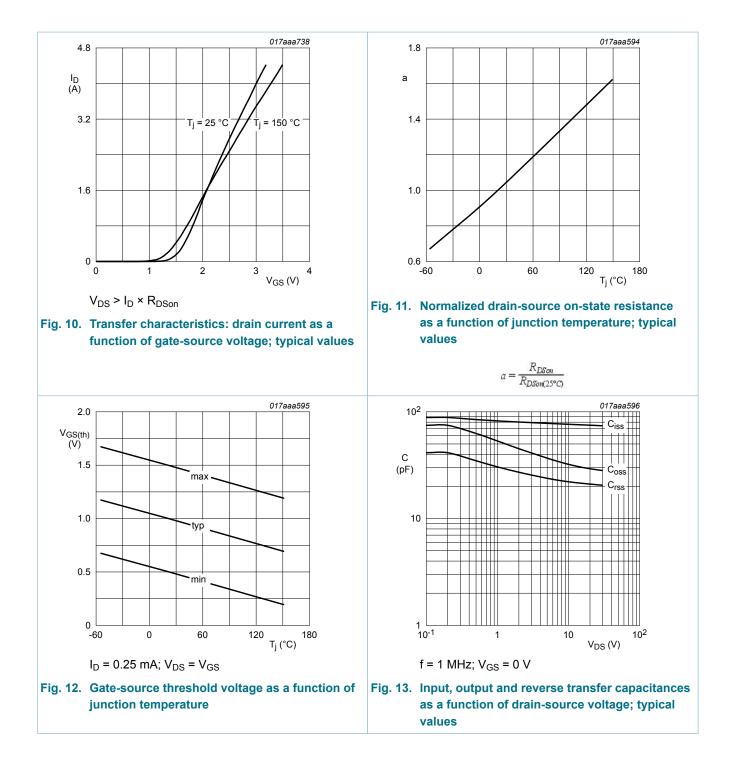
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 1.1 A; T _j = 25 °C	-	185	250	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 1.1 A; T _j = 150 °C	-	300	400	mΩ
		V_{GS} = 2.5 V; I _D = 0.25 A; T _j = 25 °C	-	255	365	mΩ
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 1.1 A; T _j = 25 °C	-	2.9	-	S
Dynamic cl	haracteristics	· · · · · ·	I			
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I _D = 1.1 A; V _{GS} = 4.5 V;	-	0.87	1.3	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.17	-	nC
Q _{GD}	gate-drain charge	-	-	0.24	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	76	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	30	-	pF
C _{rss}	reverse transfer capacitance	-	-	22	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; I _D = 1.1 A; V _{GS} = 4.5 V;	-	7	-	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	11	-	ns
t _{d(off)}	turn-off delay time		-	16	-	ns
t _f	fall time		-	7	-	ns
Source-dra	in diode		I			
V _{SD}	source-drain voltage	I _S = 0.7 A; V _{GS} = 0 V; T _i = 25 °C	-	0.8	1.2	V

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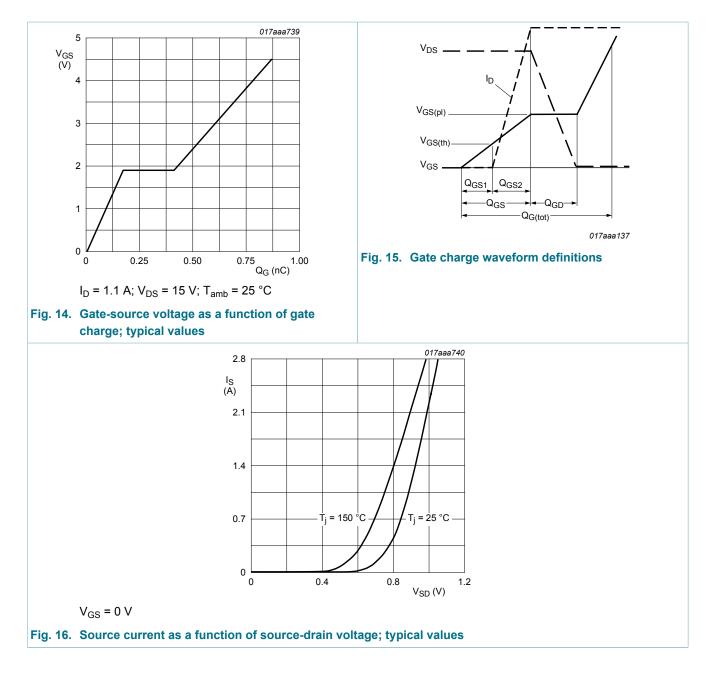
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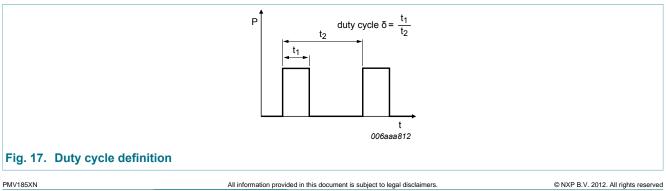
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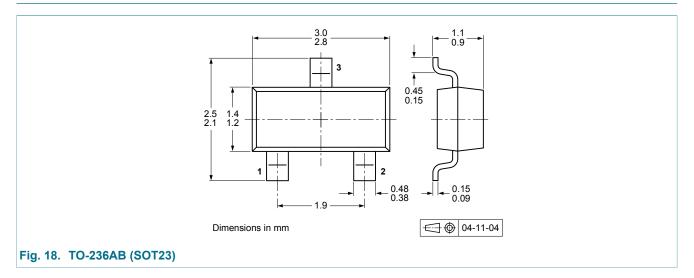


Test information 8.

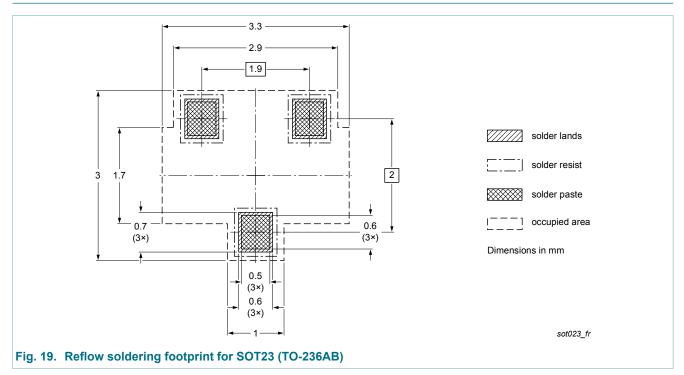


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9. Package outline

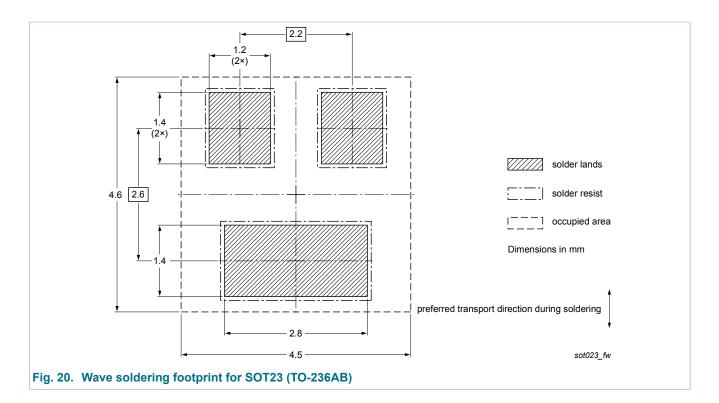


10. Soldering



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11. Revision history

Table 8.Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV185XN v.1	20120803	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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